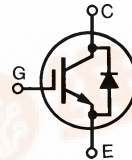




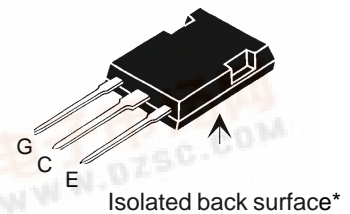
Low $V_{CE(sat)}$ IGBT with Diode ISOPLUS247™ (Electrically Isolated Back Surface)

$V_{CES} = 600\text{ V}$
 $I_{C25} = 75\text{ A}$
 $V_{CE(sat)} = 1.7\text{ V}$

Preliminary data



Symbol	Test Conditions	Maximum Ratings	ISOPLUS247™
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1\text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	75	A
I_{C100}	$T_C = 90^\circ\text{C}$	60	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	200	A
SSOA (RBSOA)	$V_{GE} = 15\text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 10\ \Omega$ Clamped inductive load; $V_{CL} = 0.8 V_{CES}$	$I_{CM} = 100$	A
P_C	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ..+ 150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55...+ 150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
V_{ISOL}	50/60Hz, RMS, t = 1minute, leads-to tab	2500	V
Weight		5	g



G = Gate, C = Collector,
E = Emitter, TAB = Collector

* Patent pending

Features

- Silicon chip on Direct-Copper-Bond substrate
- High power dissipation
- Isolated mounting surface
- 2500V electrical isolation
- Low collector to tab capacitance (<25pF)
- Rugged polysilicon gate cell structure
- Fast intrinsic Rectifier
- Low $V_{CE(sat)}$ IGBT and standard diode for minimum on-state conduction losses
- MOS Gate turn-on for drive simplicity

Applications

- Solid state relays
- Capacitor discharge circuits
- High power ignition circuits

Advantages

- Space savings (two devices in one package)
- Reduces assembly time and cost
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 1\text{ mA}$, $V_{GE} = 0\text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250\ \mu\text{A}$, $V_{CE} = V_{GE}$	2.5		5.5 V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0\text{ V}$			$T_J = 25^\circ\text{C}$: 250 μA $T_J = 150^\circ\text{C}$: 2 mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C100}$, $V_{GE} = 15\text{ V}$			1.7 V



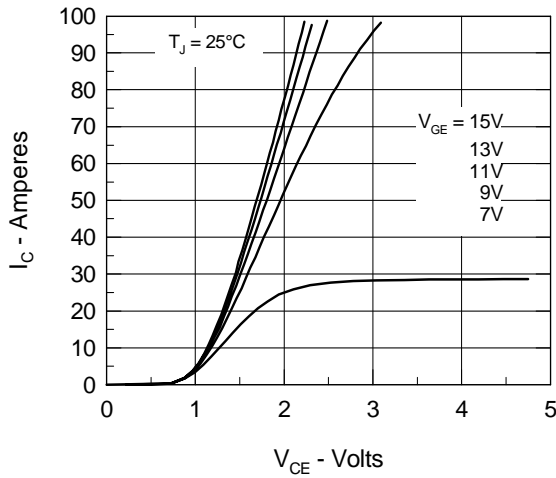


Figure 1. Saturation Voltage Characteristics

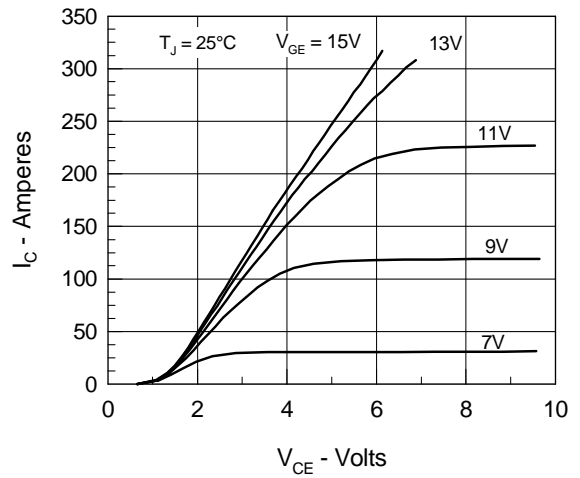


Figure 2. Extended Output Characteristics

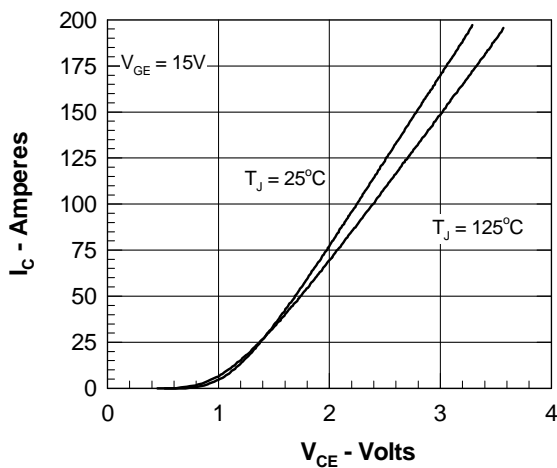


Figure 3. Saturation Voltage Characteristics

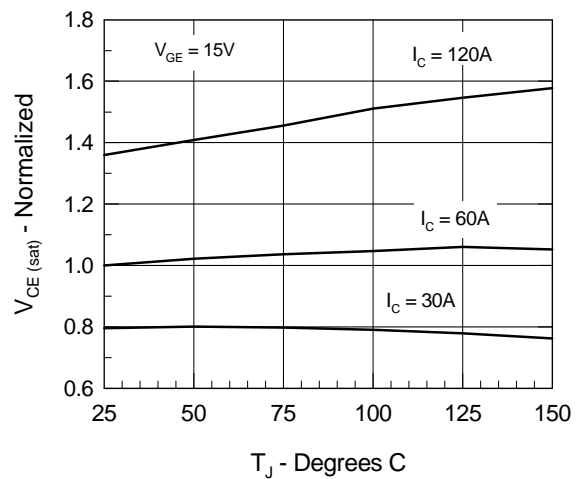
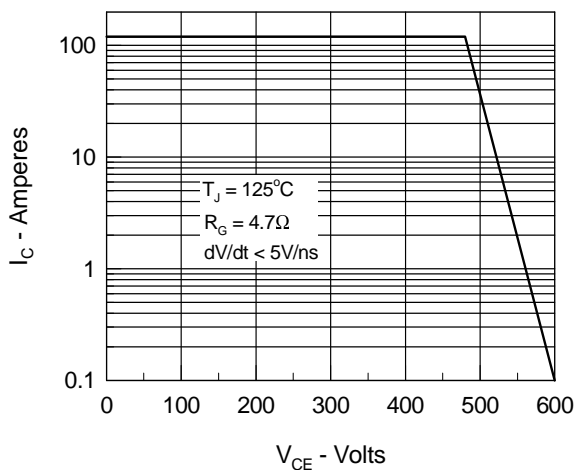

 Figure 4. Temperature Dependence of $V_{CE(sat)}$


Figure 5. Admittance Curves

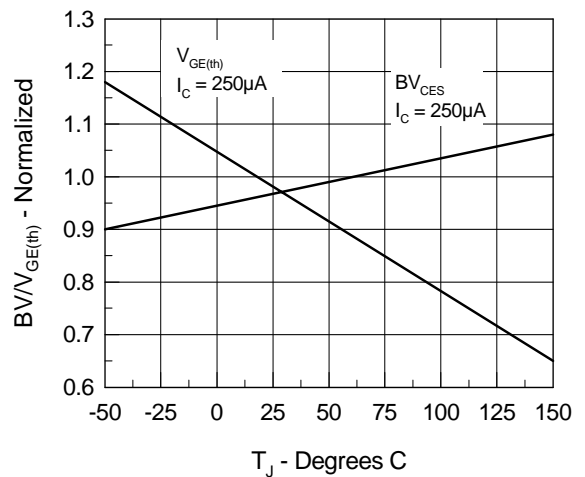


Figure 6. Capacitance Curves

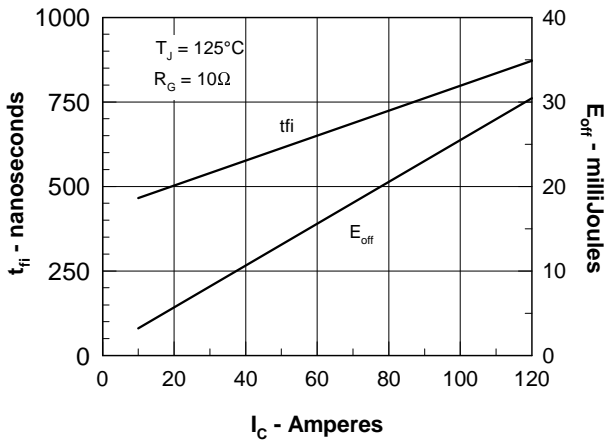


Figure 7. Dependence of E_{ON} and E_{OFF} on I_C .

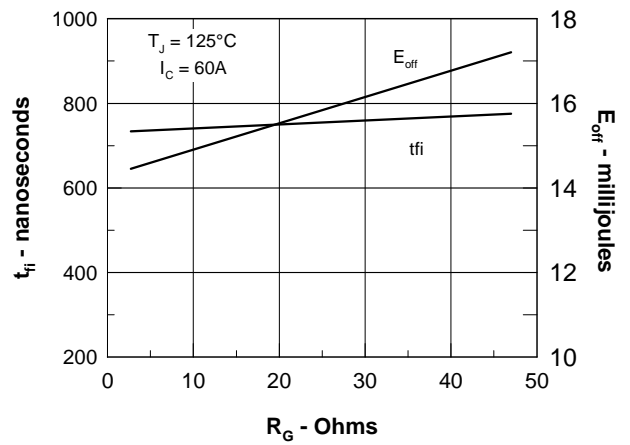


Figure 8. Dependence of E_{ON} and E_{OFF} on R_G .

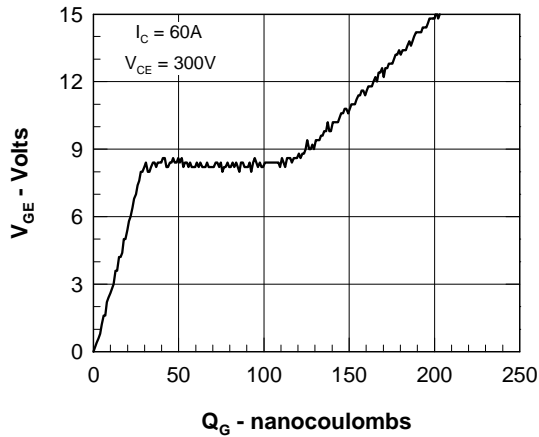


Figure 9. Gate Charge

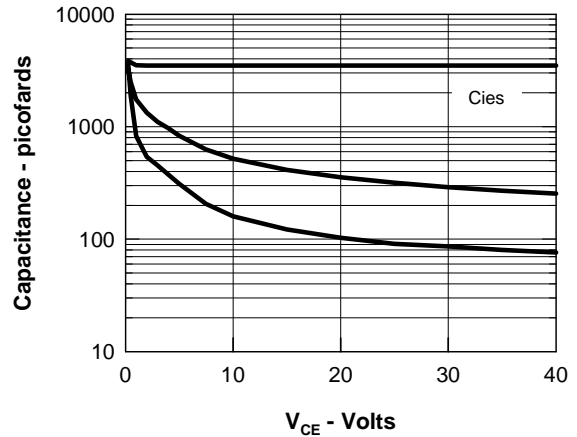


Figure 10. Turn-off Safe Operating Area

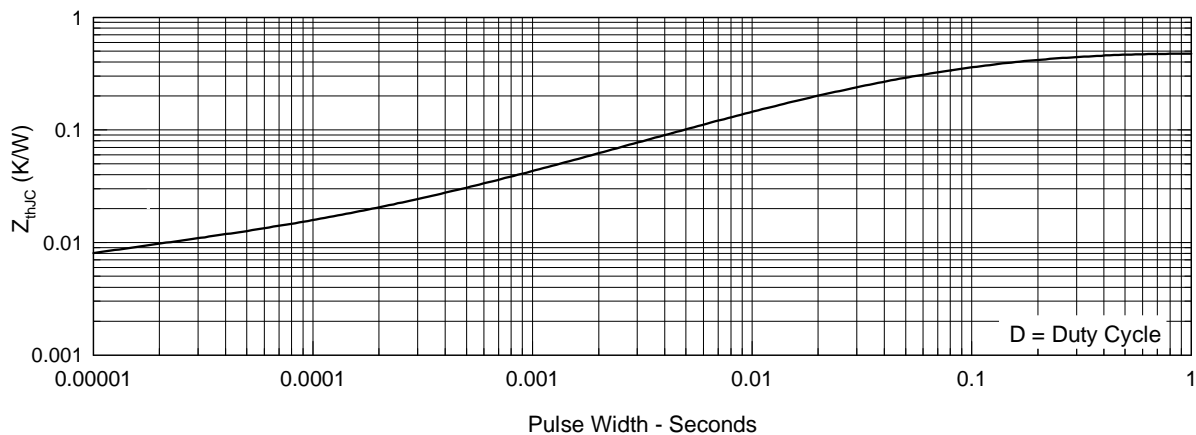


Figure 11. IGBT Transient Thermal Resistance

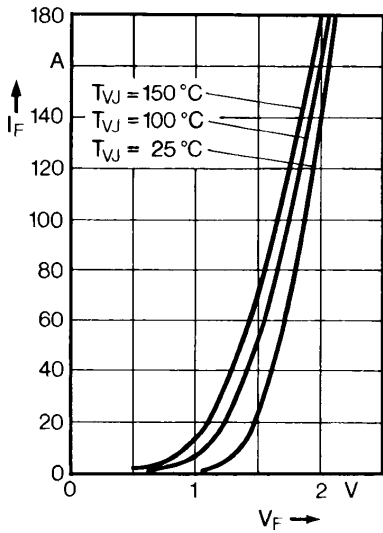


Fig. 12 Forward current versus voltage drop.

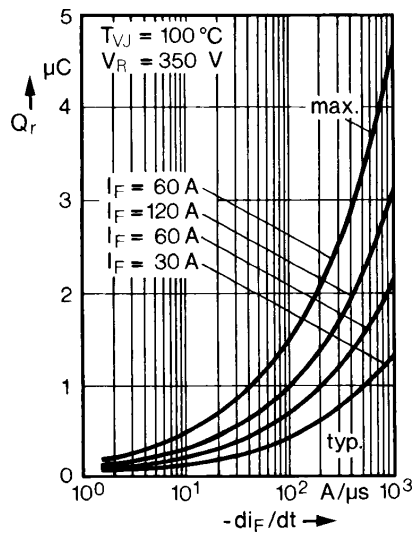


Fig. 13 Recovery charge versus $-di_F/dt$.

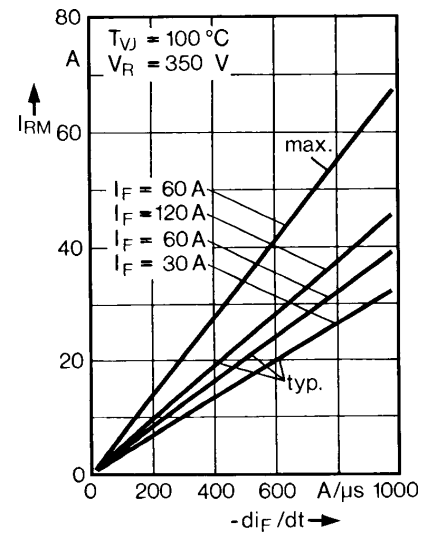


Fig. 14 Peak reverse current versus $-di_F/dt$.

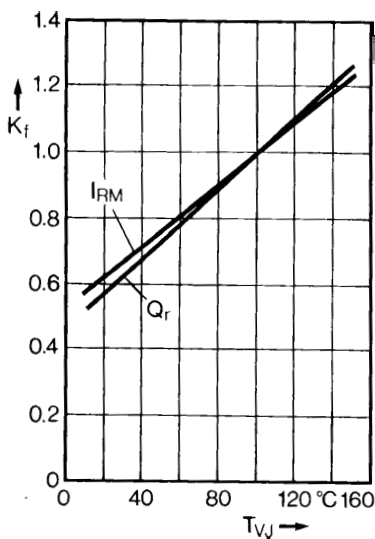


Fig. 15 Dynamic parameters versus junction temperature.

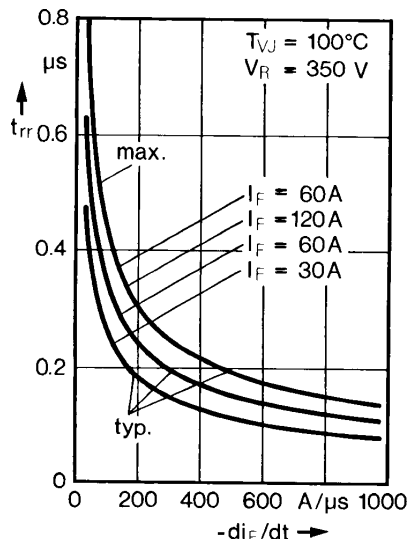


Fig. 16 Recovery time versus $-di_F/dt$.

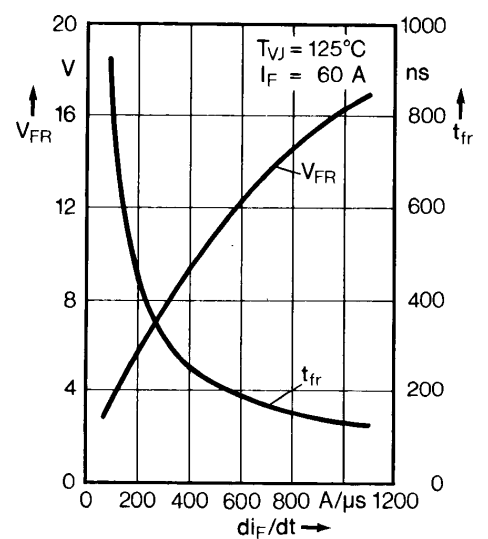


Fig. 17 Peak forward voltage vs. di_F/dt .

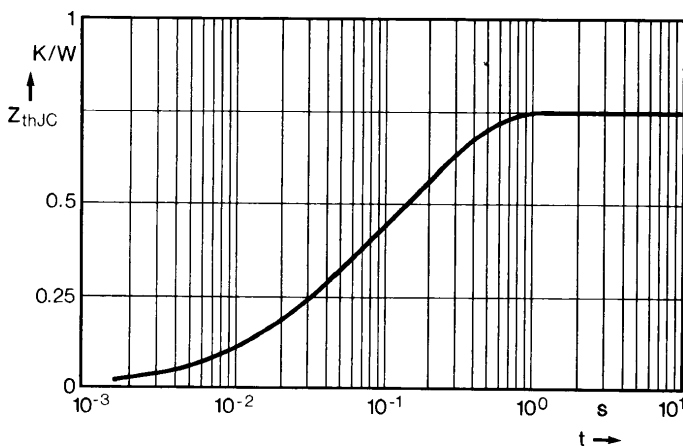


Fig. 18 Transient thermal impedance junction to case.